**Blue** are new market stabilizing/positive leaning info. **Orange** are new neutral/negative info.

| Device | Company | Production Profile | Comments |
|---|---|---|---|
| NAND | Overall NAND | | 3xxL ramping in 2025. Technology upgrades to manage supply, bit growth recovering. |
| | Samsung | Vol.: 236L<br>Ramp: 286L | - VEU (Validated End-User) waiver revoked for advanced tools into China<br>- Upgrading Xi'an to V8/V9; P4 NAND delayed to 2026 |
| | Kioxia/Sandisk | Vol: 218L | - Kitakami Fab 2 started ops in Sept. with 'meaningful output' in 1H'26.<br>- WD divested NAND into Sandisk; 2025 joint CapEx $1.9B (-25% vs. 2024) |
| | SK Hynix | Vol.: 321L | - Volume production of 321L QLC Q3'25<br>- VEU exemption status revoked by BIS impacting Dalian |
| | Micron | Vol.: 232L | - Revised 2025 NAND CapEx down, upgrades to manage supply |
| | YMTC | Vol: 232L | - Started ramping 294L in Q1'25; +15% capacity expansion targeted for E'26<br>- "All-Chinese" OEM pilot line planned in 2H'25<br>- >300L challenged by U.S. export restrictions for advanced tools |
| DRAM | Overall DRAM | | HBM driving expanded DRAM spend to support AI; 4F$^2$ development in progress |
| | Samsung | Vol: 1b nm,<br>Ramp: 1c nm | - Ongoing CapEx for expanding EUV capacity in Pyeongtaek P3<br>- Expanding 1c capacity for HBM4 to P4 & migrate H17 from 1z → 1c |
| | SK Hynix | Vol: 1b nm,<br>Ramp: 1c nm | - VEU exemption status revoked by BIS for Wuxi fab<br>- Accelerating M15x build-out, 2025 CapEx increase incl. Korea fab build<br>- Focusing spend on high bandwidth memory (1b/1c node) to meet AI demand |
| | Micron | Vol: 1$\beta$ nm<br>Ramp: 1$\gamma$ nm | - Targeting 2025 CapEx to be 30% of revenues, majority for DRAM/HBM<br>- Japan fab upgrading capabilities to support 1$\gamma$ nm production.<br>- Additional CapEx announced (+$30B through 2045) for US mfg onshoring.<br>- New Boise fab & Singapore assembly/test on track (2027) |
| | ChangXin Mem. Tech. (CXMT) | 1y ramp<br>1z delay | - Fab2 (Hefei) ramping; not on entities list but nearing BIS node limit<br>- Delayed volume DDR5 to E'25; HBM development ongoing, expected 2026 |
| | Other Memory | HBM<br>1x | - YMTC: development to enter DRAM space targeting HBM products.<br>- Nanya: new fab 2026 ramp expected<br>- Winbond: slow Kaohsiung P1 (20K) ramp |
| Foundry/Logic | Foundry/Logic | | Leading & trailing nodes investment planned. Fab utilization recovering. |
| Foundry/Logic ≤16nm | TSMC | 3nm | - FY'25 CapEx to $40+B; indicated ~$>40B spending in 2026+<br>- Total US investment $165B, AZ ramp accelerated again for strong demand<br>- AZ (Fab1 4nm, 2025; F2 3nm, 2026; F3 2nm, 2027), Japan fab2 (6nm, 2027) |
| | Intel | 4nm<br>≤14nm | - '25/'26 CapEx cut; Ohio TBD; CHIPs grant converted to U.S. equity stake<br>- AZ 18A production started Q3'25; foundry securing contracts on 18A node |
| | Samsung | 3nm GAA | - Reduced CapEx in '25. Taylor TX construction resumed, ops target 2026.<br>- Yongin fab complex planned, target building 5 logic fabs in 20 years ($230B) |
| | Rapidus | 2nm GAA | - Production goal for 2027, $3-4B CapEx '25 → ~$8B 2026. |
| | GlobalFoundries | 14nm | - Malta new fab planned, timing TBD. |
| | SMIC | <14nm | - Delivering 7/5nm to Chinese chipmakers to circumvent US restrictions |
| Foundry/Logic ≥20nm | TSMC | 22/28nm<br>12/16nm | - Japan fab revised timeline to realign target technologies to market.<br>- Dresden JV fab (groundbreaking Aug'24, ramp 2027-end) |
| | UMC | 28nm | - 2025 CapEx revised to ~$1.8B, Singapore production pushed to 2026 |
| | SMIC | 28nm | - Continuing high spending level with ~$7B forecast for 2025 |
| | Powerchip | >28nm | - Ramp of new Tongluo (+19K); Technology license sale to Tata (India) |
| | GlobalFoundries | 28nm, FDSOI | - Announced 2x capacity expansion of Dresden fab to be completed by 2032.<br>- Collaboration with ST put on hold. |
| | Other | >28nm | - US: TI announced 2 additional fabs for Sherman (SM3&4) to long-term plan.<br>- China: CanSemi (Guangzhou, +40K wmp), Hua Hong (Wuxi, $6.7B +30K), Wingsky (Shanghai, 45K), Zensemi (MEMS, Quangshou), CR Micro (Shenzhen)<br>- Japan: Toshiba (P2 '26), slowed/inactive: Renesas; Rohm, Sanken, Sony.<br>- Europe: ST (Crolles on hold); Infineon (Dresden, 2026)<br>- India: Tata (2026 expected operations start) |
| Packaging | TSMC | - | - $4-8B (10-20% CapEx), incl. expanding CoWoS capacity to support AI demand<br>- US Adv. packaging fabs (constr. 2027) |
| | Intel | | - Consolidating sites (closing Costa Rica); canceled Poland plan (2027). |
| | GlobalFoundries | | - Adding adv. pkg & test expansion to Malta |
| | SK Hynix | | - HBM fab in Indiana (2028) |